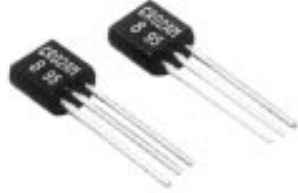


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LOW POWER USE
PLANAR PASSIVATION TYPE

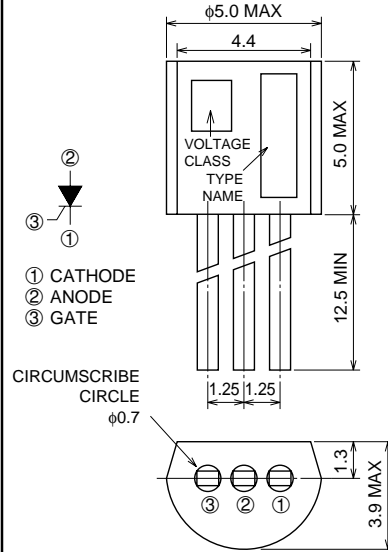
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- I_T (AV) **0.3A**
- V_{DRM} **200V/300V/400V**
- I_{GT} **100 μ A**

OUTLINE DRAWING

Dimensions
in mm



JEDEC : TO-92

APPLICATION

Solid state relay, leakage protector, fire alarm, timer, ringcounter, electric blankets, strobe flasher, other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class			Unit
		4	6	8	
V_{RRM}	Repetitive peak reverse voltage	200	300	400	V
V_{RSM}	Non-repetitive peak reverse voltage	300	400	500	V
V_R (DC)	DC reverse voltage	160	240	320	V
V_{DRM}	Repetitive peak off-state voltage *1	200	300	400	V
V_D (DC)	DC off-state voltage *1	160	240	320	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current		0.47	A
I_T (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction, $T_a=30^\circ\text{C}$	0.3	A
I_{TSM}	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	10	A
I^2t	I^2t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	0.4	A ² s
PGM	Peak gate power dissipation		0.1	W
PG (AV)	Average gate power dissipation		0.01	W
V_{FGM}	Peak gate forward voltage		6	V
V_{RGM}	Peak gate reverse voltage		6	V
I_{FGM}	Peak gate forward current		0.1	A
T_j	Junction temperature		-40 ~ +125	°C
T_{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	0.23	g

*1. With Gate-to-cathode resistance $R_{GK}=1\text{k}\Omega$

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LOW POWER USE
PLANAR PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

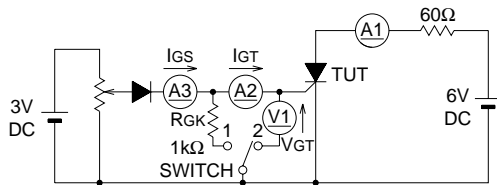
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	$T_J=125^\circ\text{C}$, V_{RRM} applied	—	—	0.1	mA
IDRM	Repetitive peak off-state current	$T_J=125^\circ\text{C}$, V_{DRM} applied, $R_{GK}=1\text{k}\Omega$	—	—	0.1	mA
V _{TM}	On-state voltage	$T_a=25^\circ\text{C}$, $I_{TM}=0.6\text{A}$, instantaneous value	—	—	1.6	V
V _{GT}	Gate trigger voltage	$T_a=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$ *3	—	—	0.8	V
V _{GD}	Gate non-trigger voltage	$T_J=125^\circ\text{C}$, $V_D=1/2V_{DRM}$, $R_{GK}=1\text{k}\Omega$	0.2	—	—	V
I _{GT}	Gate trigger current	$T_J=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$ *3	1	—	100*2	μA
I _H	Holding current	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$, $R_{GK}=1\text{k}\Omega$	—	—	3	mA
R _{th(j-a)}	Thermal resistance	Junction to ambient	—	—	180	°C/W

*2. If special values of I_{GT} are required, choose at least two items from those listed in the table below. (Example: AB, BC)

Item	A	B	C
I _{GT} (μA)	1 ~ 30	20 ~ 50	40 ~ 100

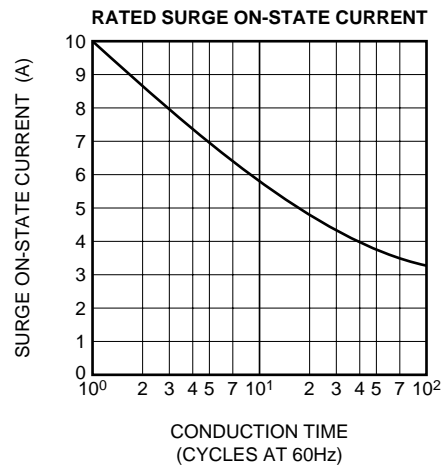
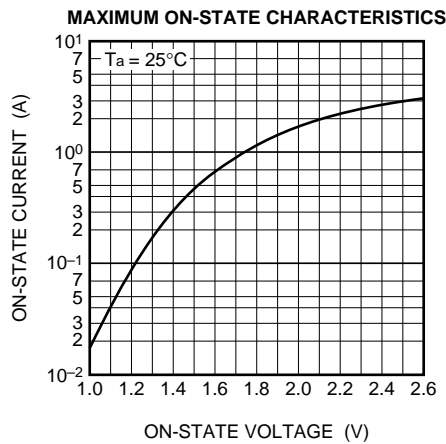
The above values do not include the current flowing through the 1kΩ resistance between the gate and cathode.

*3. I_{GT}, V_{GT} measurement circuit.



SWITCH 1 : I_{GT} measurement
SWITCH 2 : V_{GT} measurement
(Inner resistance of voltage meter is about 1kΩ)

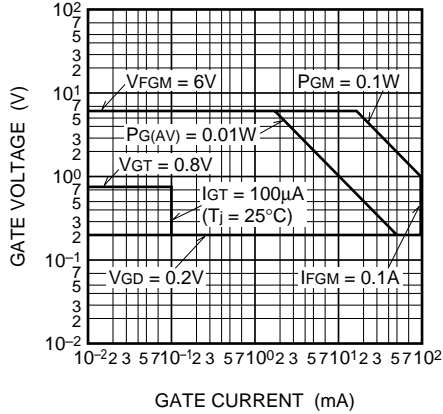
PERFORMANCE CURVES



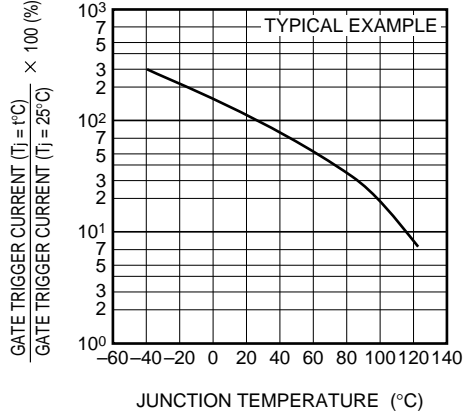
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LOW POWER USE
PLANAR PASSIVATION TYPE

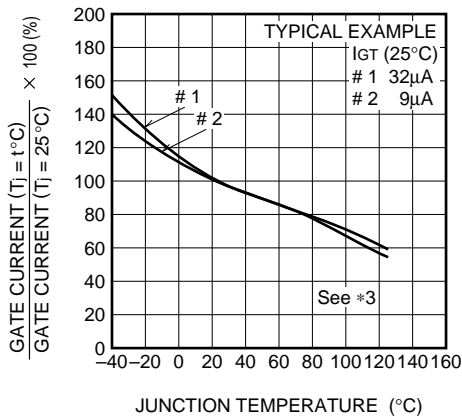
GATE CHARACTERISTICS



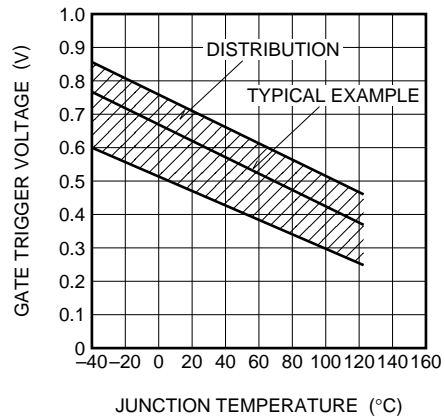
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



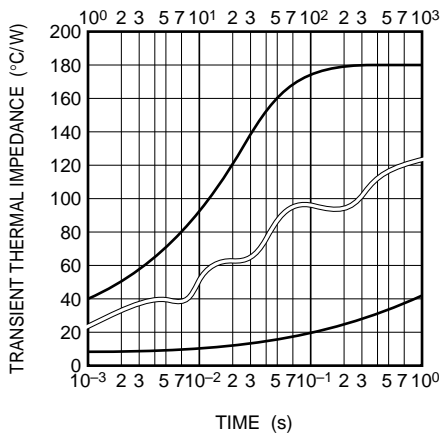
GATE CURRENT VS. JUNCTION TEMPERATURE



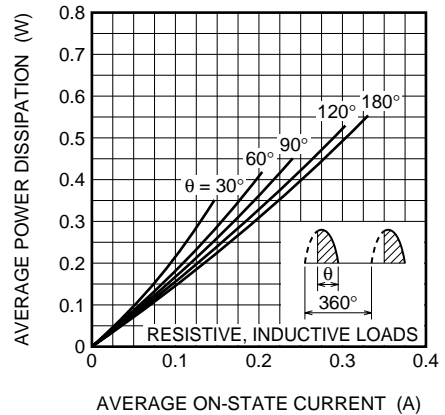
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)



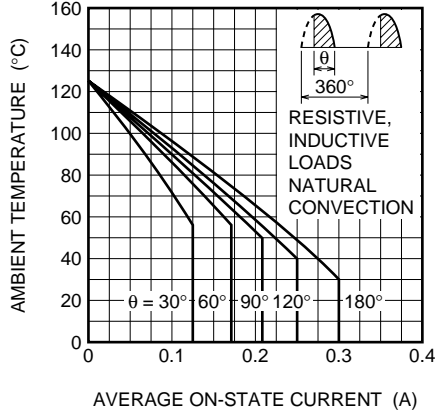
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE HALF WAVE)



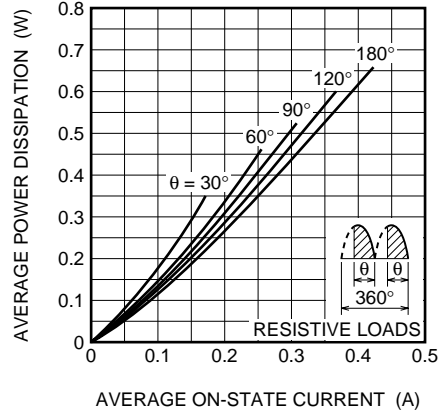
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LOW POWER USE
PLANAR PASSIVATION TYPE

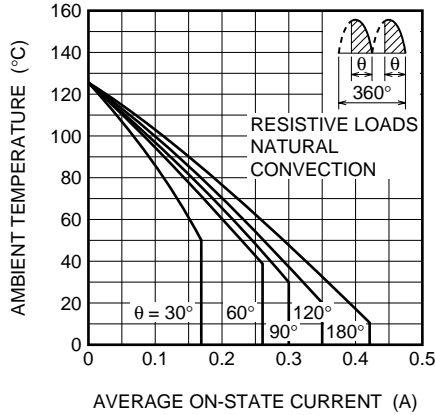
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



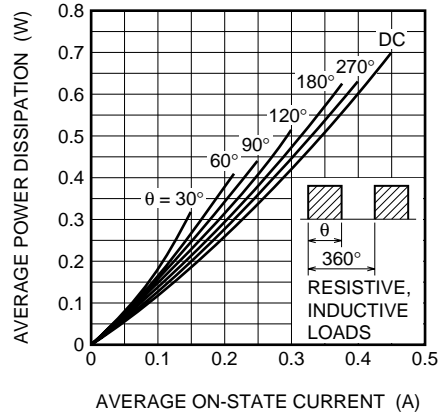
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE FULL WAVE)



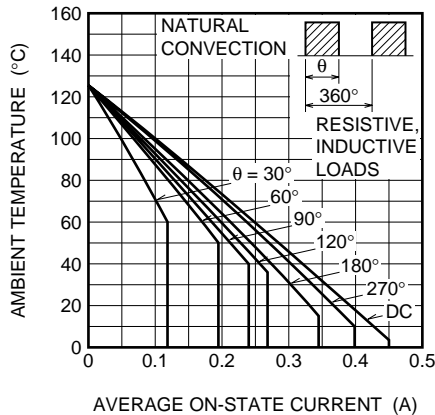
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)



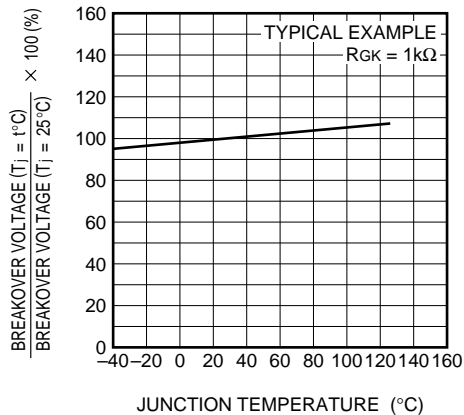
MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



CR02AM

LOW POWER USE
PLANAR PASSIVATION TYPE

